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CHUNG et al.(10) **Pub. No.: US 2018/0151118 A1**(43) **Pub. Date: May 31, 2018**(54) **ORGANIC LIGHT EMITTING DIODE
DISPLAY DEVICE**(52) **U.S. CL.**CPC **G09G 3/3233** (2013.01); **G09G 3/3275**
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2310/0264 (2013.01); **H01L 27/3262**
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Sung-Hun KIM, Iksan-si (KR)(21) Appl. No.: **15/672,952**

(57)

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An organic light emitting diode (OLED) display device for simplifying a structure of an internal compensation pixel circuit is disclosed. The OLED display device is configured in such a way that an N^{th} pixel circuit shares a transistor for initializing a storage capacitor and a gate electrode of a driving transistor that belong to an $(N+1)^{th}$ pixel circuit to initialize an OLED element. Accordingly, a transistor for initializing an OLED element is omitted from each pixel circuit, thereby simplifying a circuit structure and reducing a circuit area.

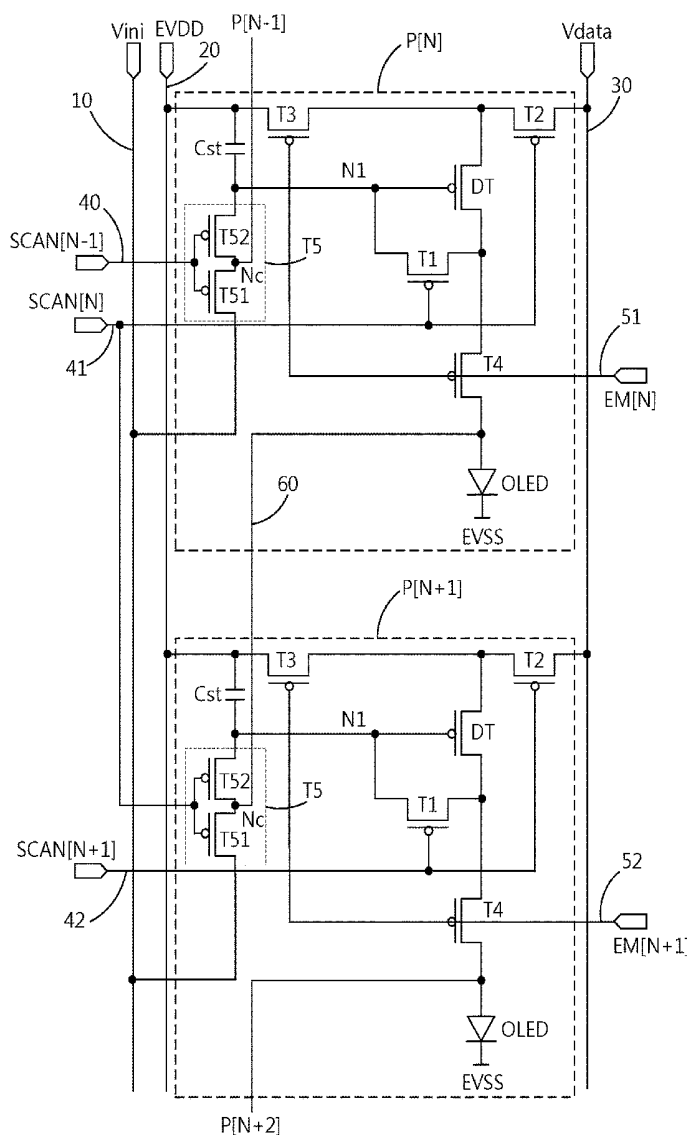


FIG. 1

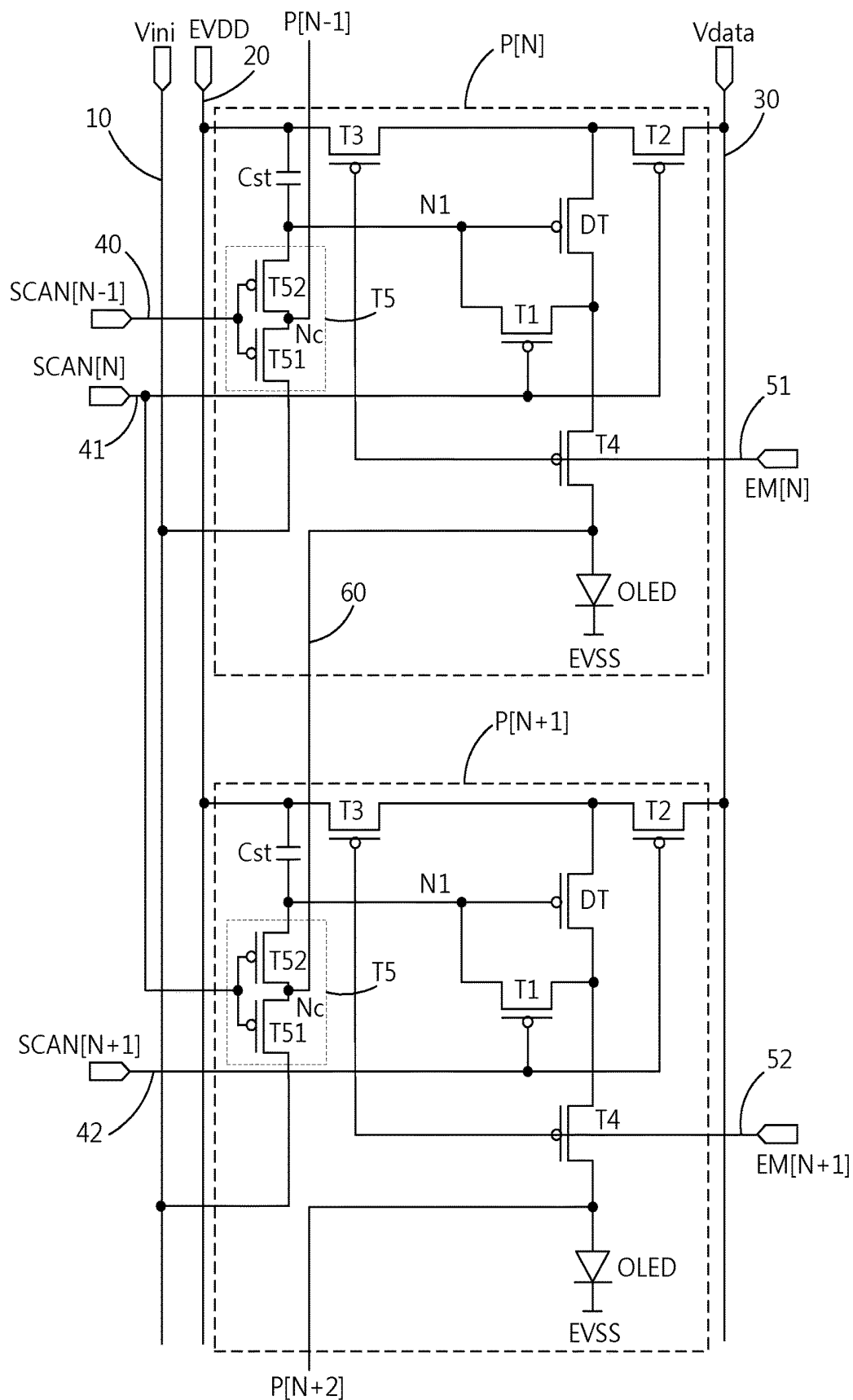


FIG. 2

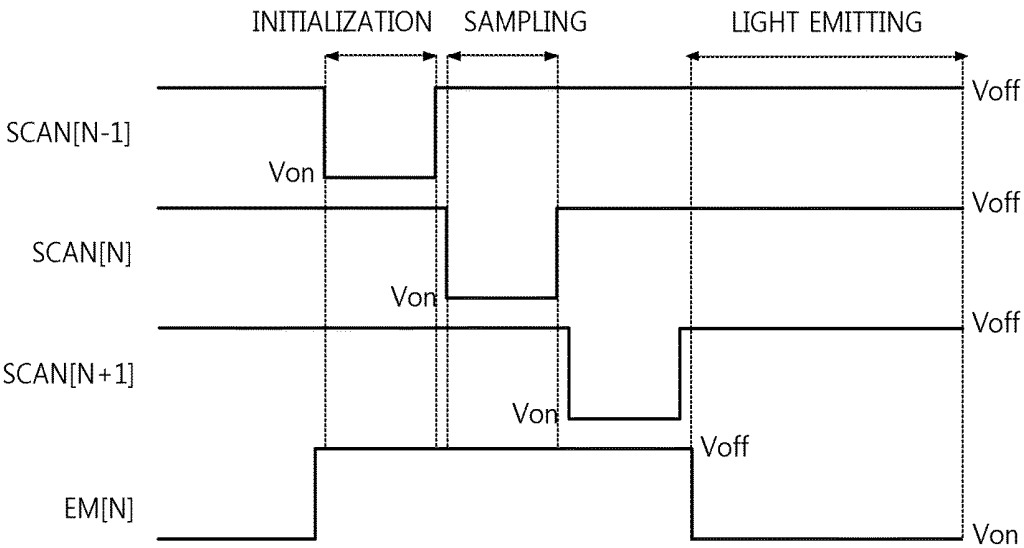


FIG. 3A

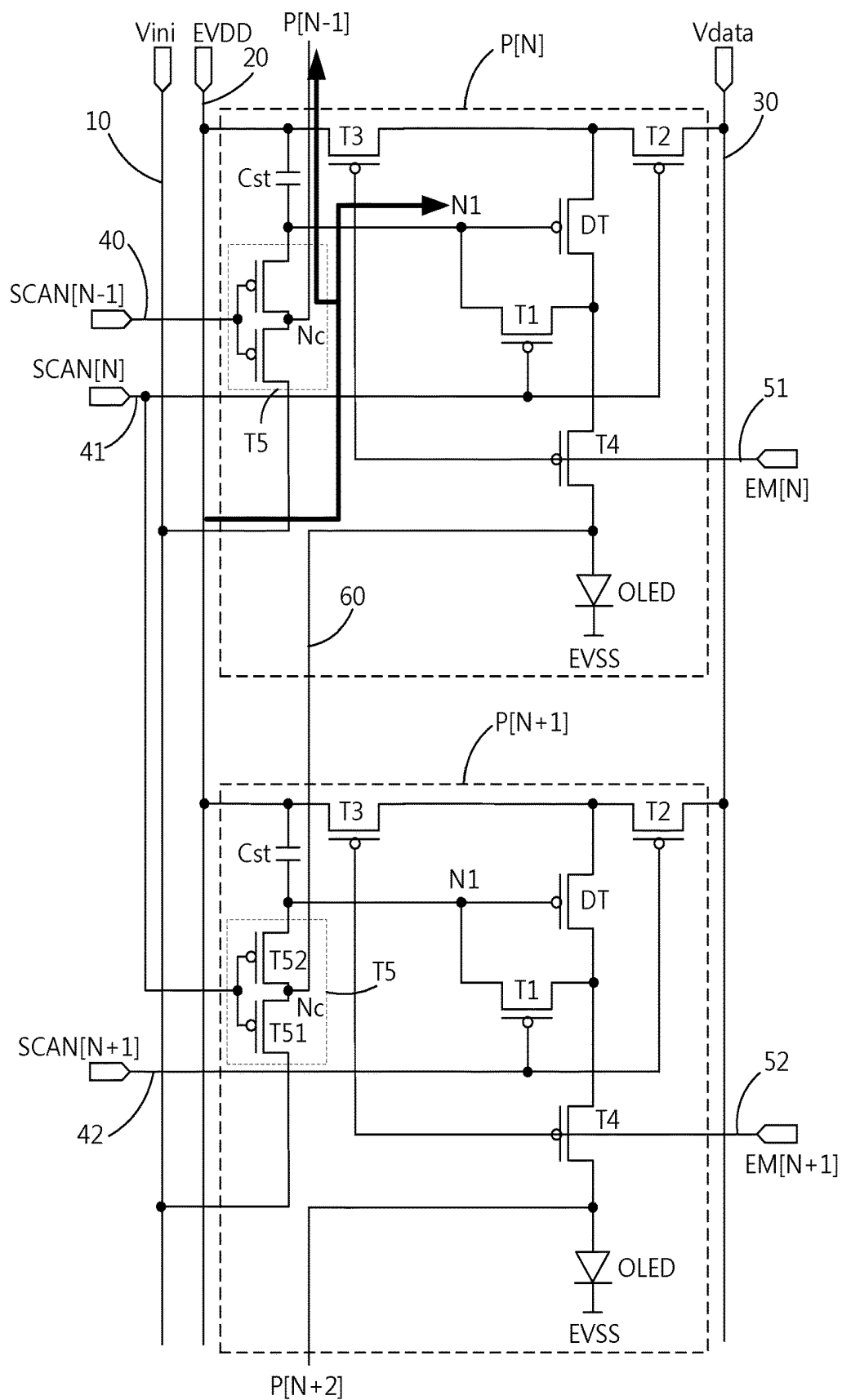


FIG. 3B

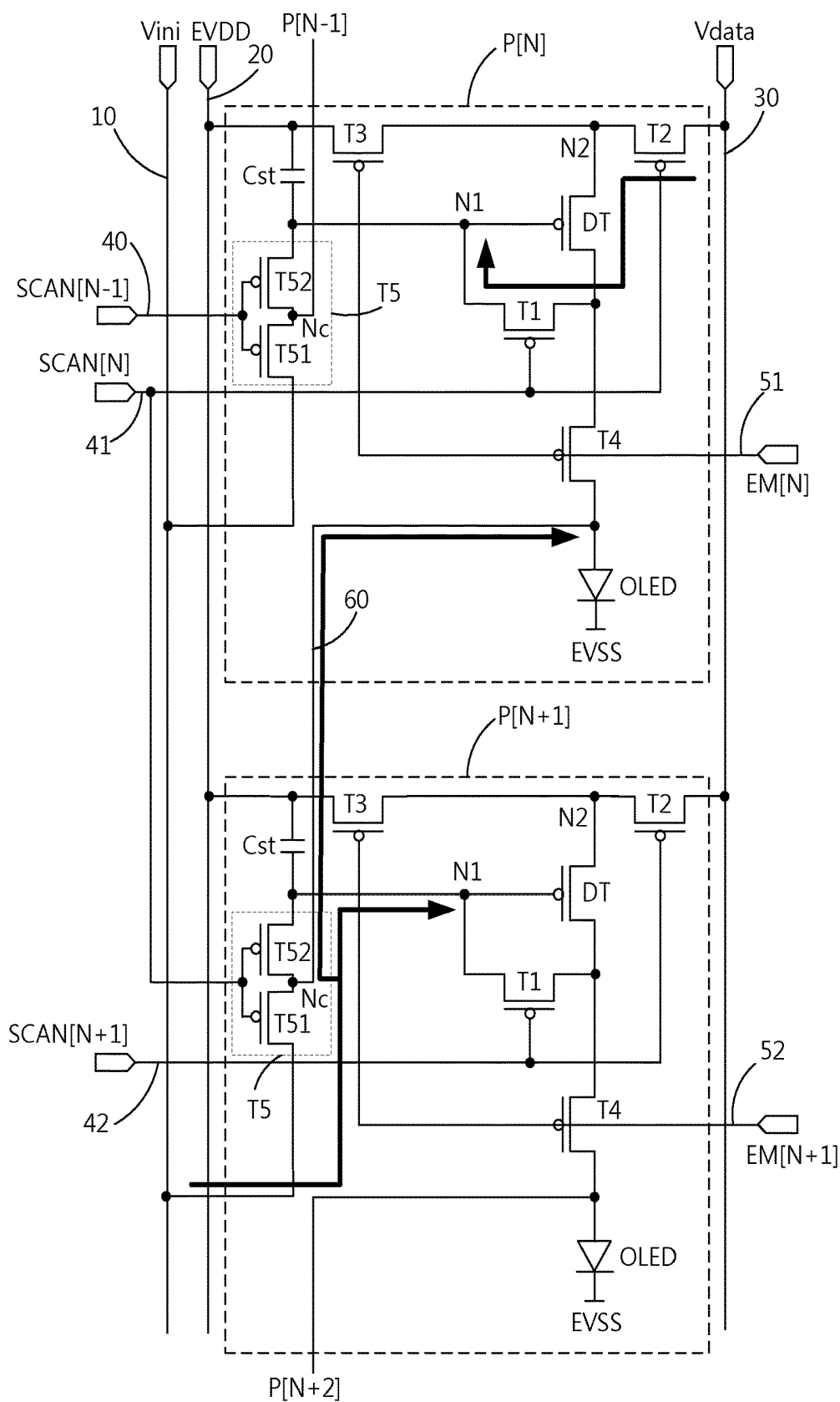


FIG. 4

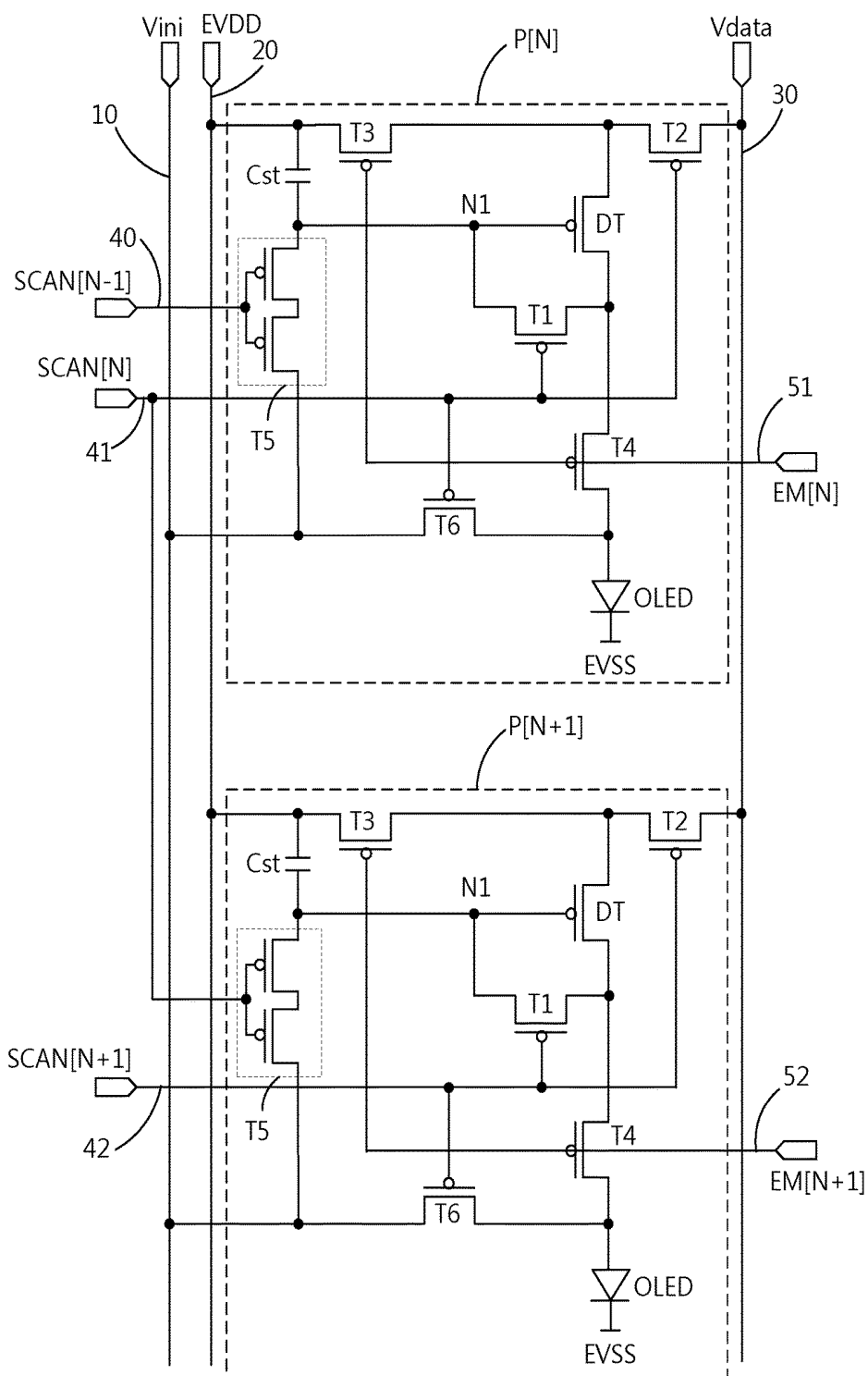


FIG. 5

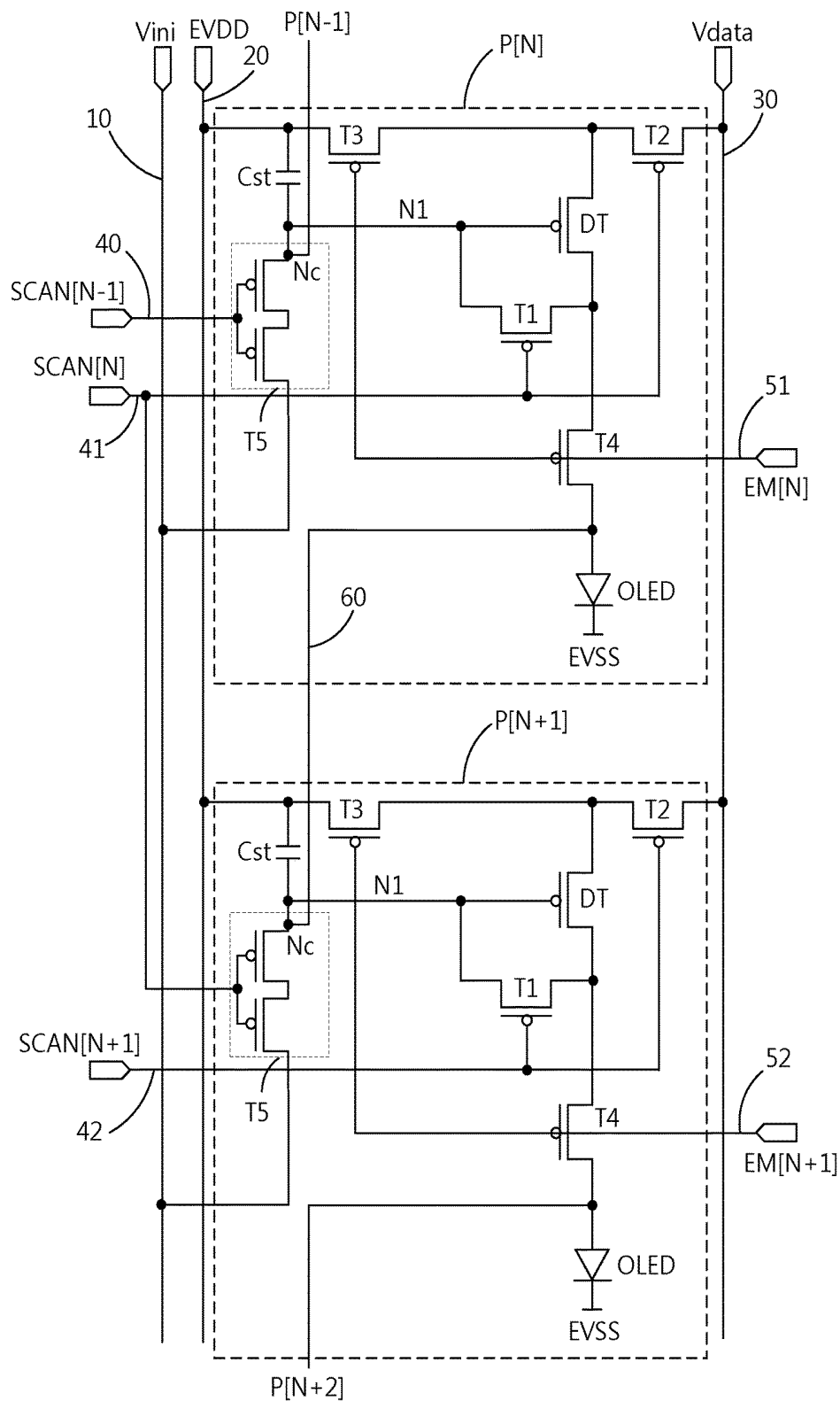
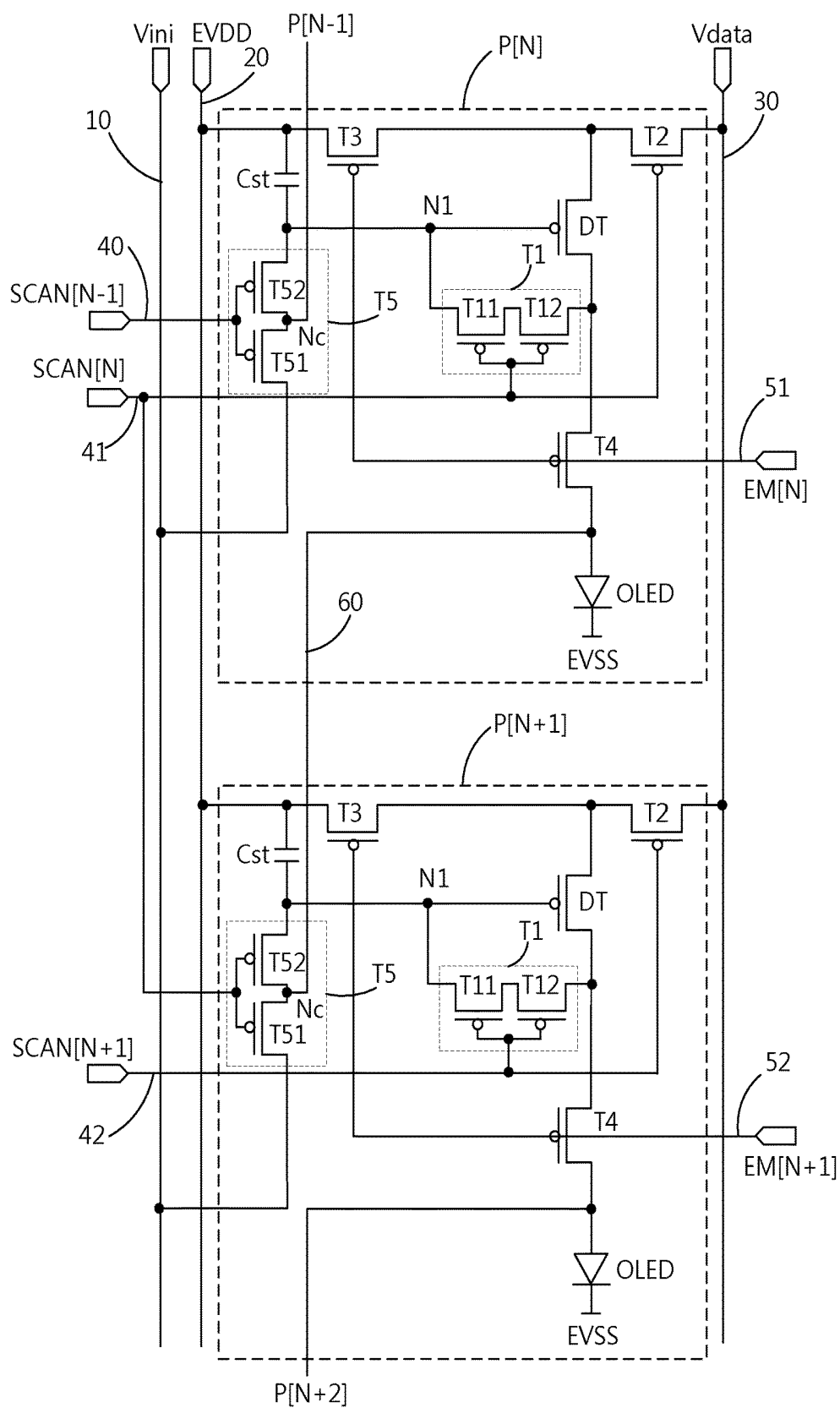


FIG. 7



**ORGANIC LIGHT EMITTING DIODE
DISPLAY DEVICE****CROSS-REFERENCE TO RELATED
APPLICATIONS**

[0001] This application claims the benefit of Republic of Korea Patent Application No. 10-2016-0162344, filed on Nov. 30, 2016, which is hereby incorporated by reference in its entirety.

BACKGROUND**Field of Technology**

[0002] The present disclosure relates to an organic emitting diode display device for simplifying a structure of an internal compensation pixel circuit.

Discussion of the Related Art

[0003] Recently, a liquid crystal display (LCD) using liquid crystal, an organic light emitting diode (OLED) display device using an OLED, an electrophoretic display (EPD) using electrophoretic particles, etc. have been representatively used as a flat display device for displaying an image by using digital data.

[0004] There among, an OLED display device is a self-emitting device configured in such a way that an organic light emitting layer emits light via recombination between electrons and holes and is expected as a next-generation display device in terms of high brightness, low driving voltage, and an ultra thin film.

[0005] Each of a plurality of pixels included in an OLED display device includes an OLED element and a pixel circuit for independently driving the OLED element. The pixel circuit adjusts current I_{ds} for driving the OLED element by a driving transistor by a driving voltage V_{gs} corresponding to a data signal to adjust brightness of the OLED element.

[0006] With regard to an OLED display device, characteristics such as a threshold voltage value (hereinafter, V_{th}) of a driving transistor are irregular for each respective pixel and, thus, current I_{ds} with respect to the same driving voltage V_{gs} is changed, thereby causing brightness deviation.

[0007] To overcome this, an internal compensation technology of an OLED display device for compensating for V_{th} of a driving transistor in each pixel circuit and driving the driving transistor using a data signal, V_{th} of which is compensated for, has been proposed.

[0008] However, a pixel circuit having an internal compensation function includes a plurality of transistors and, thus, a pixel circuit disadvantageously has a complex structure. For example, a high resolution model of quad high definition (QHD) or more has been known as using an internal compensation pixel circuit of a 7T1C structure including seven transistors and one capacitor.

[0009] Accordingly, a conventional internal compensation pixel circuit has a limit in reducing an area occupied by a pixel circuit due to a plurality of transistor structures. Accordingly, it is difficult to enhance pixels per inch (ppi) along with increase in resolution and, thus, it is difficult to apply a high-resolution display device.

SUMMARY

[0010] Accordingly, the present disclosure is directed to an organic light emitting diode display device that substantially obviates one or more problems due to limitations and disadvantages of the related art.

[0011] An object of the present disclosure is to provide an organic light emitting diode display device for simplifying a structure of an internal compensation pixel circuit.

[0012] Additional advantages, objects, and features of the invention will be set forth in part in the description which follows and in part will become apparent to those having ordinary skill in the art upon examination of the following or may be learned from practice of the invention. The objectives and other advantages of the invention may be realized and attained by the structure particularly pointed out in the written description and claims hereof as well as the appended drawings.

[0013] To achieve these objects and other advantages and in accordance with the purpose of the disclosure, as embodied and broadly described herein, an organic light emitting diode (OLED) display device is configured in such a way that an N^{th} pixel circuit shares a transistor for initializing a storage capacitor and a gate electrode of a driving transistor that belong to an $(N+1)^{th}$ pixel circuit to initialize a light emitting element. Accordingly, a transistor for initializing a light emitting element may be omitted from each pixel circuit, thereby simplifying a circuit structure and reducing a circuit area.

[0014] In an aspect of the present disclosure, an organic light emitting diode (OLED) display device includes a plurality of pixel circuits, each of the plurality of pixel circuits including a light emitting element, a driving transistor configured to drive the light emitting element depending on a driving voltage, a first transistor configured to connect a first electrode and a gate electrode of the driving transistor in response to a scan signal of an N^{th} (N is a natural number) scan line, a second transistor configured to supply a data voltage of a data line to a second electrode of the driving transistor in response to a scan signal of the N^{th} scan line, a third transistor configured to supply a first supply voltage of a power line to the second electrode of the driving transistor in response to a light emitting control signal of an N^{th} light emitting control line, a fourth transistor configured to connect the driving transistor to the light emitting element in response to a light emitting control signal of the N^{th} light emitting control line, a fifth transistor configured to initialize a first node to which a gate electrode of the driving transistor and a storage capacitor are connected, to an initialization voltage of an initialization voltage supplying line, in response to a scan signal of an $(N-1)^{th}$ scan line, and the storage capacitor connected between the power line and the first node and configured to store a driving voltage of the driving transistor.

[0015] A light emitting element of an N^{th} pixel circuit connected to the N^{th} scan line and the $(N-1)^{th}$ scan line among the plurality of pixel circuits may be connected to a fifth transistor of an $(N+1)^{th}$ pixel circuit connected to the N^{th} scan line and the next $(N+1)^{th}$ scan line through a connection electrode.

[0016] It is to be understood that both the foregoing general description and the following detailed description of the present invention are exemplary and explanatory and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

[0017] The accompanying drawings, which are included to provide a further understanding of the disclosure and are incorporated in and constitute a part of this application, illustrate embodiment(s) of the invention and together with the description serve to explain the principle of the invention. In the drawings:

[0018] FIG. 1 is an equivalent circuit diagram illustrating a pixel circuit structure of an organic light emitting diode (OLED) display device according to an embodiment of the present disclosure;

[0019] FIG. 2 is a driving waveform diagram of a pixel circuit according to an embodiment of the present disclosure;

[0020] FIGS. 3A to 3C are diagrams sequentially illustrating a driving procedure of a pixel circuit according to an embodiment of the present disclosure;

[0021] FIG. 4 is a diagram illustrating a pixel circuit according to the related art compared with the embodiment of the present disclosure shown in FIG. 1;

[0022] FIG. 5 is an equivalent circuit diagram showing a pixel circuit structure of an OLED display device according to an embodiment of the present disclosure;

[0023] FIG. 6 is an equivalent circuit diagram showing a pixel circuit structure of an OLED display device according to an embodiment of the present disclosure; and

[0024] FIG. 7 is an equivalent circuit diagram showing a pixel circuit structure of an OLED display device according to an embodiment of the present disclosure.

DETAILED DESCRIPTION

[0025] FIG. 1 is an equivalent circuit diagram illustrating a pixel circuit structure of an organic light emitting diode (OLED) display device according to an embodiment of the present invention.

[0026] Referring to FIG. 1, the OLED display device may include an N^{th} pixel circuit P[N] and an $(N+1)^{th}$ pixel circuit P[N+1] that are sequentially scanned and share some transistor T5.

[0027] The pixel circuits P[N] and P[N+1] may be connected to an initialization voltage supplying line 10 for supplying an initialization voltage Vini, a first power line 20 for supplying a high voltage supply voltage EVDD, and a data line 30 for supplying a data voltage Vdata. The N^{th} pixel circuit P[N] may be connected to an $(N-1)^{th}$ scan line 40, an N^{th} scan line 41, and an N^{th} light emitting control line 51 and the $(N+1)^{th}$ pixel circuit P[N+1] may be connected to the N^{th} scan line 41, an $(N+1)^{th}$ scan line 42, and an $(N+1)^{th}$ light emitting control line 52.

[0028] Each of the pixel circuits P[N] and P[N+1] may include first to fifth transistors T1 to T5, a driving transistor DT, and a storage capacitor Cst and may independently drive an OLED element. All the transistors T1 to T5 and DT of the pixel circuits P[N] and P[N+1] may be implemented with a P-channel or N-channel type thin film transistor TFT. According to the following embodiments, an example in which all the transistors DT and T1 to T5 are implemented with only a P-channel type TFT will be described but an N-channel type TFT may also be applied.

[0029] The N^{th} and $(N+1)^{th}$ pixel circuits P[N] and P[N+1] may have the same circuit structure except that only control lines for controlling respective transistors, that is, a scan line and a light emitting control line are sequentially changed.

Hereinafter, a detailed structure and driving procedure of a pixel circuit will be described with reference to the N^{th} pixel circuit P[N].

[0030] An OLED element of the N^{th} pixel circuit P[N] may include an anode connected to the driving TFT DT, a cathode connected to a low voltage supply voltage EVSS, and a light emitting layer between the anode and the cathode and generate light, the amount of which is proportional to the amount of current supplied from the driving TFT DT.

[0031] A first electrode of the storage capacitor Cst of the N^{th} pixel circuit P[N] may be connected to the first power line 20 and a second electrode may be connected to a first node N1 connected to a gate electrode of the driving transistor DT so as to be charged with a driving voltage Vgs of the driving transistor DT.

[0032] The driving transistor DT of the N^{th} pixel circuit P[N] may control current for driving an OLED element by the driving voltage Vgs stored in the storage capacitor Cst.

[0033] A first transistor T1 of the N^{th} pixel circuit P[N] may be controlled by a scan signal SCAN[N] of the N^{th} scan line 41 and a gate electrode and a drain electrode of the driving transistor DT may be connected to connect the driving transistor DT to a diode structure during a sampling period of the N^{th} pixel circuit P[N].

[0034] A second transistor T2 of the N^{th} pixel circuit P[N] may be controlled by the scan signal SCAN[N] of the N^{th} scan line 41 and may supply the data voltage Vdata of the data line 30 to a source electrode of the driving transistor DT during a sampling period of the N^{th} pixel circuit P[N].

[0035] A third transistor T3 of the N^{th} pixel circuit P[N] may be controlled by a light emitting control signal EM[N] of the N^{th} light emitting control line 51 and may supply a high voltage supply voltage EVDD of a first power line 20 to a source electrode of the driving transistor DT during a light emitting period of the N^{th} pixel circuit P[N].

[0036] A fourth transistor T4 of the N^{th} pixel circuit P[N] may be controlled by the light emitting control signal EM[N] of the N^{th} light emitting control line 51 and may supply driving current supplied from the driving transistor DT to the OLED element during a light emitting period of the N^{th} pixel circuit P[N].

[0037] A fifth transistor T5 of the N^{th} pixel circuit P[N] may be controlled by a scan signal SCAN[N-1] of the $(N-1)^{th}$ scan line 40 and may initialize the first node N1 connected to the storage capacitor Cst and a gate electrode of the driving transistor DT to an initialization voltage Vini during an initialization period of the N^{th} pixel circuit P[N].

[0038] The fifth transistor T5 may be configured as a dual gate transistor in that a fifth transistor pair T51 and T52 which share a gate and are connected in series forms a direct current path according to control of connected dual gates, as shown in FIG. 1. The dual gate structure of fifth transistor T5 may suppress unstable current and may stably initialize the first node N1.

[0039] In particular, an OLED element of the N^{th} pixel circuit P[N] may be connected to the fifth transistor T5 of the $(N+1)^{th}$ pixel circuit P[N+1] through a connection electrode 60 and initialized by the fifth transistor T5 of the $(N+1)^{th}$ pixel circuit P[N+1]. Accordingly, during a sampling period of the N^{th} pixel circuit P[N] that overlaps an initialization period of the $(N+1)^{th}$ pixel circuit P[N+1], an anode of the OLED element of the N^{th} pixel circuit P[N] may be initial-

ized by the initialization voltage V_{ini} through the connection electrode **60** and the fifth transistor **T5** of the $(N+1)^{th}$ pixel circuit $P[N+1]$.

[0040] For example, in the fifth transistor pair **T51** and **T52** of a dual gate that belongs to the $(N+1)^{th}$ pixel circuit $P[N+1]$, a connection node N_c between **T51** and **T52** may be connected to an anode of the OLED element of the N^{th} pixel circuit $P[N]$ through the connection electrode **60**.

[0041] Based on the same principle, the dual gate structure of fifth transistor **T5** that belongs to the N^{th} pixel circuit $P[N]$ may be connected to an anode of an OLED element of an $(N-1)^{th}$ pixel circuit $P[N-1]$ through the connection node N_c and the connection electrode **60** to initialize the first node $N1$ of the N^{th} pixel circuit $P[N]$ by an initialization voltage V_{ini} and to also initialize an anode of the OLED element of the $(N-1)^{th}$ pixel circuit $P[N-1]$ by the initialization voltage V_{ini} .

[0042] As such, according to an embodiment of the present disclosure, the N^{th} pixel circuit $P[N]$ may share the transistor **T5** for initializing a storage capacitor C_{st} and a gate electrode of the driving transistor **DT** that belongs to the $(N+1)^{th}$ pixel circuit $P[N+1]$ to initialize an OLED element. Accordingly, each pixel circuit does not require an additional transistor for initializing an OLED element, thereby simplifying a circuit structure and reducing a circuit area.

[0043] FIG. 2 is a driving waveform diagram of a pixel circuit according to an embodiment of the present disclosure. FIGS. 3A to 3C are diagrams sequentially illustrating a driving procedure of a pixel circuit according to an embodiment of the present disclosure.

[0044] Referring to FIG. 2, the scan signal $SCAN[N-1]$ of the $(N-1)^{th}$ scan line **40**, the scan signal $SCAN[N]$ of the N^{th} scan line **41**, and the scan signal $SCAN[N+1]$ of the $(N+1)^{th}$ scan line **42** may supply a scan pulse of a gate on voltage V_{on} during respective scan periods of corresponding scan lines that are sequentially shifted and supply a gate off voltage V_{off} during the remaining period. The light emitting control signal $EM[N]$ of the N^{th} light emitting control line **51** may supply the gate off voltage V_{off} during a non-emitting period that overlaps scan periods of the $(N-1)^{th}$, N^{th} , and $(N+1)^{th}$ scan lines **40**, **41**, and **42** and supply the gate on voltage V_{on} during the remaining emitting period.

[0045] To control the P-channel type transistors **T1** to **T5** shown in FIG. 1, in FIG. 2, the gate on voltage V_{on} may be supplied at a low level and the gate off voltage V_{off} may be supplied at a high level. When the transistors **T1** to **T5** shown in FIG. 1 are configured as an N-channel type transistor, the gate on voltage V_{on} may be supplied at a high level and the gate off voltage V_{off} may be supplied at a low level, oppositely to FIG. 2.

[0046] Referring to FIGS. 2 and 3A, during an initialization period of the N^{th} pixel circuit $P[N]$, the fifth transistor **T5** may be turned on in response to the scan signal $SCAN[N-1]$ of the $(N-1)^{th}$ scan line **40** to initialize the first node $N1$ of the N^{th} pixel circuit $P[N]$ to an initialization voltage V_{ini} and to also initialize an anode of an OLED element of the $(N-1)^{th}$ pixel circuit $P[N-1]$ to an initialization voltage V_{ini} . During the initialization period, the first to fourth transistors **T1** to **T4** of the N^{th} pixel circuit $P[N]$ and the driving transistor **DT** may be turned off.

[0047] Referring to FIGS. 2 and 3B, during a sampling period of the N^{th} pixel circuit $P[N]$, the first and second transistors **T1** and **T3** may be turned on in response to the scan signal $SCAN[N]$ of the N^{th} scan line **41**. During the

sampling period, the second transistor **T2** may supply the data voltage V_{data} of the data line **30** to a source element of the driving transistor **DT** and the first transistor **T1** may connect a gate electrode and a drain electrode of the driving transistor **DT** such that the driving transistor **DT** operates as a diode structure. Since V_{th} is compensated for by an operation of a diode of the driving transistor **DT**, a data voltage " $V_{data}-V_{th}$ " obtained by compensating for V_{th} may be supplied to the gate electrode of the driving transistor **DT**. Accordingly, the storage capacitor C_{st} may be charged by a driving voltage " $V_{gs}=EVDD-V_{data}+V_{th}$ " to which the data voltage " $V_{data}-V_{th}$ " obtained by compensating for V_{th} is applied and may supply the driving voltage " $V_{gs}=EVDD-V_{data}+V_{th}$ " to the driving transistor **DT** during a next light emitting period. During the sampling period, the third to fifth transistors **T3** to **T5** may be turned-off.

[0048] In particular, during a sampling period of the N^{th} pixel circuit $P[N]$, the fifth transistor **T5** of the $(N+1)^{th}$ pixel circuit $P[N+1]$ may be turned on in response to the scan signal $SCAN[N]$ of the N^{th} scan line **41** and, while the first node $N1$ of the $(N+1)^{th}$ pixel circuit $P[N+1]$ is initialized by an initialization voltage V_{ini} , an anode of an OLED element of the N^{th} pixel circuit $P[N]$ may also be initialized by the initialization voltage V_{ini} through the connection electrode **60**.

[0049] Referring to FIGS. 2 and 3C, during a light emitting period of the N^{th} pixel circuit $P[N]$, the third and fourth transistors **T3** and **T4** may be turned on in response to the light emitting control signal $EM[N]$ of the N^{th} light emitting control line **51**. During the light emitting period, the third transistor **T3** may supply the high voltage supply voltage $EVDD$ of the first power line **20** to a source electrode of the driving transistor **DT** and the fourth transistor **T4** may supply driving current supplied from the driving transistor **DT** to an OLED element such that an OLED element emits light.

[0050] In this case, the driving transistor **DT** may supply driving current I_{oled} to an OLED element using the driving voltage $V_{gs}=EVDD-V_{data}+V_{th}$ stored in the storage capacitor C_{st} . The driving current I_{oled} of the OLED element may be determined according to " $EVDD-V_{data}$ " by offsetting a component V_{th} of the driving transistor **DT** according to Equation 1 below. In Equation 1 below, k is a proportional coefficient including mobility of the driving transistor **DT** and a component of channel width W /length L .

[Equation 1]

[0051]

$$I_{oled}=k(V_{gs}-V_{th})^2=k\{EVDD-V_{data}+V_{th}-V_{th}\}^2=k(EVDD-V_{data})^2$$

[0052] As such, according to an embodiment of the present disclosure, since the N^{th} pixel circuit $P[N]$ and the $(N+1)^{th}$ pixel circuit $P[N+1]$ may share the fifth transistor **T5**, an additional transistor for initializing an OLED element is not required and, thus, each pixel circuit may be simplified as a 6T1C structure including six transistors and one capacitor.

[0053] FIG. 4 is a diagram illustrating a pixel circuit according to the related art compared with the embodiment of the present disclosure shown in FIG. 1.

[0054] As seen from FIG. 4, each of the N^{th} pixel circuit $P[N]$ and the $(N+1)^{th}$ pixel circuit $P[N+1]$ according to the

related art includes a sixth transistor T6 for initializing an anode of an OLED element and, thus, has a 7T1C structure including seven transistors and one transistor.

[0055] The sixth transistor T6 of the N^{th} pixel circuit P[N] may be turned on in response to the scan signal SCAN[N] of the N^{th} scan line 41 that controls the first and second transistors T1 and T2 during a sampling period of the N^{th} pixel circuit P[N] to initialize an anode of an OLED element of the N^{th} pixel circuit P[N] to the initialization voltage Vini.

[0056] The sixth transistor T6 of the $(N+1)^{th}$ pixel circuit P[N+1] may be turned on in response to the scan signal SCAN[N+1] of the $(N+1)^{th}$ scan line 42 during a sampling period of the $(N+1)^{th}$ pixel circuit P[N+1] to initialize an anode of an OLED element of the $(N+1)^{th}$ pixel circuit P[N+1] to the initialization voltage Vini.

[0057] As such, compared with the prior art in that each pixel circuit includes the sixth transistor T6 that initializes an OLED element, according to an embodiment of the present disclosure shown in FIG. 1, since the sixth transistor T6 may be omitted, a pixel circuit structure may be simplified and an area of a pixel circuit may be reduced and, thus, the embodiment of the present invention may be advantageously applied to a high resolution display device.

[0058] FIGS. 5 to 7 are equivalent circuit diagrams showing a pixel circuit structure of an OLED display device according to respective embodiments of the present disclosure.

[0059] Referring to FIG. 5, the connection electrode 60 connected to an anode of an OLED of the N^{th} pixel circuit P[N] may be connected to the connection node Nc between the dual gate fifth transistor T5 of the $(N+1)^{th}$ pixel circuit P[N+1] and the first node N1.

[0060] Referring to FIG. 6, the fifth transistor T5 may use a single gate transistor structure and, in this case, the connection electrode 60 connected to an anode of an OLED element of the N^{th} pixel circuit P[N] may be connected to the connection node Nc between the fifth transistor T5 of the $(N+1)^{th}$ pixel circuit P[N+1] and the first node N1.

[0061] Referring to FIG. 7, the first transistor T1 may also be configured as a dual gate structure of first transistor pair T11 and T12, thereby enhancing the device reliability of the first transistor T1.

[0062] As described above, according to an embodiment of the present disclosure, a pixel circuit of an OLED display device may share some transistors T5 with an adjacent pixel circuit, thereby simplifying an existing 7T1C structure as a 6T1C structure. Accordingly, an internal compensation pixel circuit according to an embodiment of the present disclosure may reduce an area of a pixel circuit due to the simplified circuit structure to enhance pixels per inch (ppi) and, thus, the embodiment of the present disclosure may be applied to a high resolution display device.

[0063] According to an embodiment of the present disclosure, a pixel circuit of an OLED display device may share some transistors with an adjacent pixel circuit, thereby simplifying an existing 7T1C structure as a 6T1C structure. Accordingly, an internal compensation pixel circuit according to an embodiment of the present disclosure may reduce an area of a pixel circuit due to the simplified circuit structure to enhance pixels per inch (ppi) and, thus, the embodiment of the present disclosure may be applied to a high resolution display device.

[0064] It will be apparent to those skilled in the art that various modifications and variations can be made in the

present invention without departing from the spirit or scope of the inventions. Thus, it is intended that the present invention covers the modifications and variations of this invention provided they come within the scope of the appended claims and their equivalents.

What is claimed is:

1. An organic light emitting diode (OLED) display device comprising a plurality of pixel circuits, each of the plurality of pixel circuits comprising:

- a light emitting element;
- a driving transistor configured to drive the light emitting element depending on a driving voltage;
- a first transistor configured to connect a first electrode and a gate electrode of the driving transistor in response to a scan signal of an N^{th} (N is a natural number) scan line;
- a second transistor configured to supply a data voltage of a data line to a second electrode of the driving transistor in response to a scan signal of the N^{th} scan line;
- a third transistor configured to supply a first supply voltage of a power line to the second electrode of the driving transistor in response to a light emitting control signal of an N^{th} light emitting control line;
- a fourth transistor configured to connect the driving transistor to the light emitting element in response to a light emitting control signal of the N^{th} light emitting control line;
- a fifth transistor configured to initialize a first node to which the gate electrode of the driving transistor and a storage capacitor are connected, to an initialization voltage of an initialization voltage supplying line, in response to a scan signal of an $(N-1)^{th}$ scan line; and the storage capacitor connected between the power line and the first node and configured to store a driving voltage of the driving transistor;

wherein a light emitting element of an N^{th} pixel circuit connected to the N^{th} scan line and the $(N-1)^{th}$ scan line among the plurality of pixel circuits is connected to a fifth transistor of an $(N+1)^{th}$ pixel circuit connected to the N^{th} scan line and the next $(N+1)^{th}$ scan line through a connection electrode.

2. The OLED display device of claim 1, wherein the fifth transistor of the $(N+1)^{th}$ pixel circuit initializes a first node of the $(N+1)^{th}$ pixel circuit to the initialization voltage and initializes the light emitting element of the N^{th} pixel circuit in response to the scan signal of the N^{th} scan line.

3. The OLED display device of claim 1, wherein the connection electrode is connected to an anode of the light emitting element that belongs to the N^{th} pixel circuit, and is connected to a connection node between the fifth transistor and a first node of the $(N+1)^{th}$ pixel circuit.

4. The OLED display device of claim 1, wherein at least one of the first transistor and the fifth transistor comprises one pair of transistors that share a gate and are connected in series; and

wherein, when the fifth transistor comprises the one pair of transistors, the connection electrode is connected to the anode of the light emitting element that belongs to the N^{th} pixel circuit, and is connected to an intermediate node between the one pair of fifth transistors that belong to the $(N+1)^{th}$ pixel circuit or connected to a connection node between the fifth transistor and the first node that belongs to the $(N+1)^{th}$ pixel circuit.

5. The OLED display device of claim 1, wherein, in the N^{th} pixel circuit,

during an initialization period, the fifth transistor initializes the first node to the initialization voltage, during a next sampling period of the initialization period, the second transistor supplies the data voltage to the driving transistor, the first transistor connects the driving transistor to a diode structure, and the storage capacitor stores the driving voltage in which a threshold voltage is compensated for and to which the data voltage is applied, during a next light emitting period of the sampling period, the third transistor supplies the first supply voltage to the second node and the fourth transistor connects the driving transistor and the light emitting element, and during the sampling period, the light emitting element is initialized to the initialization voltage by a fifth transistor that belongs to the $(N+1)^{th}$ pixel circuit.

* * * * *

专利名称(译)	有机发光二极管显示装置		
公开(公告)号	US20180151118A1	公开(公告)日	2018-05-31
申请号	US15/672952	申请日	2017-08-09
[标]申请(专利权)人(译)	乐金显示有限公司		
申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	LG DISPLAY CO. , LTD.		
[标]发明人	CHUNG EUI HYUN KIM SUNG HUN		
发明人	CHUNG, EUI-HYUN KIM, SUNG-HUN		
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摘要(译)

公开了一种用于简化内部补偿像素电路的结构有机发光二极管(OLED)显示装置。OLED显示装置以如下方式配置：Nth像素电路共用用于初始化存储电容器的晶体管和属于(N+1)像素电路初始化OLED元件。因此，从每个像素电路中省略了用于初始化OLED元件的晶体管，从而简化了电路结构并减小了电路面积。

